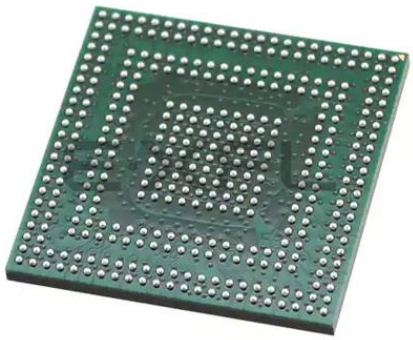

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Last Time Buy
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	200MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	369-LFBGA
Supplier Device Package	369-PBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8306svmacdca

  - The power management controller detects that the system is not idle and there are outstanding transactions on the internal bus or an external interrupt.
- Parallel I/O
  - General-purpose I/O (GPIO)
    - 56 parallel I/O pins multiplexed on various chip interfaces
    - Interrupt capability
- System timers
  - Periodic interrupt timer
  - Software watchdog timer
  - Eight general-purpose timers
- Real time clock (RTC) module
  - Maintains a one-second count, unique over a period of thousands of years
  - Two possible clock sources:
    - External RTC clock (RTC_PIT_CLK)
    - CSB bus clock
- IEEE Std. 1149.1™ compliant JTAG boundary scan

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8306S. The MPC8306S is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

The following table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic	Symbol	Max Value	Unit	Notes
Core supply voltage	V_{DD}	–0.3 to 1.26	V	—
PLL supply voltage	AV_{DD1} AV_{DD2} AV_{DD3}	–0.3 to 1.26	V	—
DDR2 DRAM I/O voltage	GV_{DD}	–0.3 to 1.98	V	—
Local bus, DUART, system control and power management, I^2C, SPI, MII, RMII, MII management, USB and JTAG I/O voltage	OV_{DD}	–0.3 to 3.6	V	2

Table 1. Absolute Maximum Ratings[1] (continued)

Characteristic		Symbol	Max Value	Unit	Notes
Input voltage	DDR2 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	3
	DDR2 DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	3
	Local bus, DUART, SYS_CLK_IN, system control and power management, I^2C, SPI, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	4
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. OVDD here refers to NVDDA, NVDDB, NVDDC, NVDDF, NVDDG, and NVDDH from the ball map.
3. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
4. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.

2.1.3 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage (V)
Local bus interface utilities signals	42	OV_{DD} = 3.3
DDR2 signal	18	GV_{DD} = 1.8
DUART, system control, I2C, SPI, JTAG	42	OV_{DD} = 3.3
GPIO signals	42	OV_{DD} = 3.3

2.1.4 Input Capacitance Specification

The following table describes the input capacitance for the SYS_CLK_IN pin in the MPC8306S.

Table 4. Input Capacitance Specification

Parameter/Condition	Symbol	Min	Max	Unit	Note
Input capacitance for all pins except SYS_CLK_IN and QE_CLK_IN	C_I	6	8	pF	—
Input capacitance for SYS_CLK_IN and QE_CLK_IN	C_{ICLK_IN}	10	—	pF	1

Note:
1. The external clock generator should be able to drive 10 pF.

2.2 Power Sequencing

The device does not require the core supply voltage (V_{DD}) and I/O supply voltages (GV_{DD} and OV_{DD}) to be applied in any particular order. Note that during power ramp-up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there might be a period of time that all input and output pins are actively driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD} and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V; see Figure 3. Once both the power supplies (I/O voltage and core voltage) are stable, wait for a minimum of 32 clock cycles before negating $\overline{\text{PORESET}}$.

NOTE

There is no specific power down sequence requirement for the device. I/O voltage supplies (GV_{DD} and OV_{DD}) do not have any ordering requirements with respect to one another.

Table 15. DDR2 SDRAM Input AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of 1.8V ± 100mV.

Parameter	Symbol	Min	Max	Unit	Note
266 MHz		–750	750		

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the equation: $t_{DISKEW} = \pm(T/4 - abs(t_{CISKEW}))$ where T is the clock period and $abs(t_{CISKEW})$ is the absolute value of t_{CISKEW}.

The following figure shows the input timing diagram for the DDR controller.

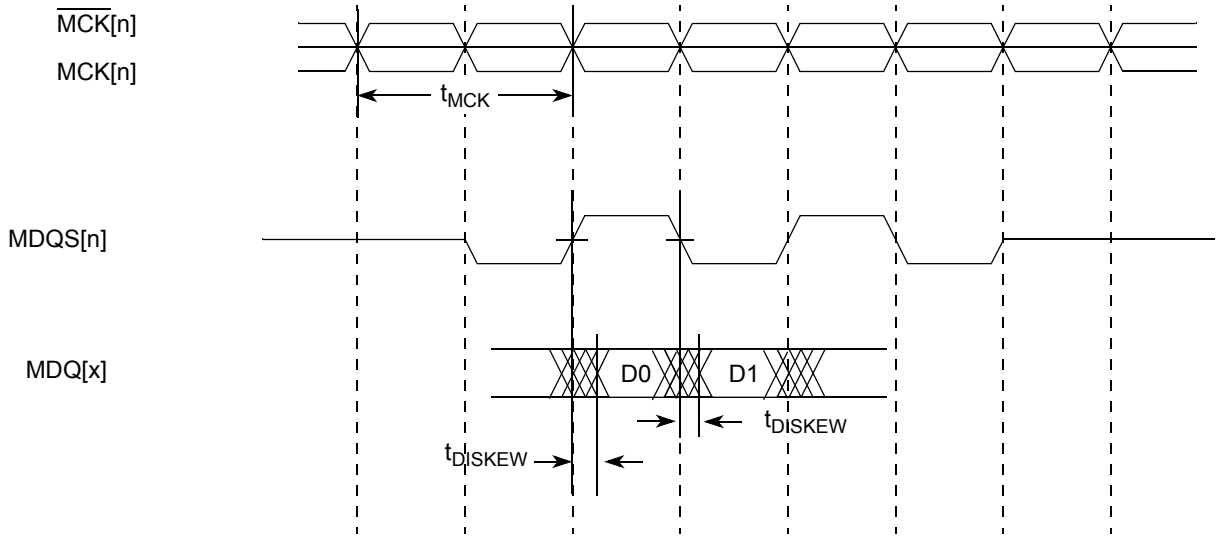

Figure 4. DDR Input Timing Diagram

6.2.2 DDR2 SDRAM Output AC Timing Specifications

The following table provides the output AC timing specifications for the DDR2 SDRAM interfaces.

Table 16. DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8V ± 100mV.

Parameter	Symbol[1]	Min	Max	Unit	Note
MCK cycle time, (MCK/$\overline{\text{MCK}}$ crossing)	t_{MCK}	5.988	8	ns	2
ADDR/CMD output setup with respect to MCK 266 MHz	t_{DDKHAS}	 2.5	 —	ns	3
ADDR/CMD output hold with respect to MCK 266 MHz	t_{DDKHAX}	 2.5	 —	ns	3
$\overline{\text{MCS}}$ output setup with respect to MCK 266 MHz	t_{DDKHCS}	 2.5	 —	ns	3

Table 16. DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of 1.8V ± 100mV.

Parameter	Symbol[1]	Min	Max	Unit	Note
$\overline{MCS}$ output hold with respect to MCK 266 MHz	t_{DDKHCX}	 2.5	 —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ/MDM output setup with respect to MDQS 266 MHz	t_{DDKHDS}, t_{DDKLDS}	 0.9	 —	ns	5
MDQ/MDM output hold with respect to MDQS 266 MHz	t_{DDKHDX}, t_{DDKLDX}	 1100	 —	ps	5
MDQS preamble start	t_{DDKHMP}	0.75 x t_{MCK}	—	ns	6
MDQS epilogue end	t_{DDKHME}	0.4 x t_{MCK}	0.6 x t_{MCK}	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{MCK}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{MCK}$, $\overline{MCS}$, and MDQ/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the Clock Control register is set to adjust the memory clocks by 1/2 applied cycle.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjusts in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8306S PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. t_{DDKHMP} follows the symbol conventions described in note 1.

The following figure provides the AC test load for the local bus.

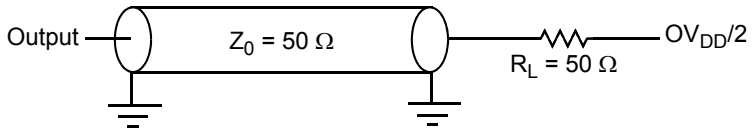

Figure 7. Local Bus AC Test Load

The following figures show the local bus signals. These figures has been given indicate timing parameters only and do not reflect actual functional operation of interface.

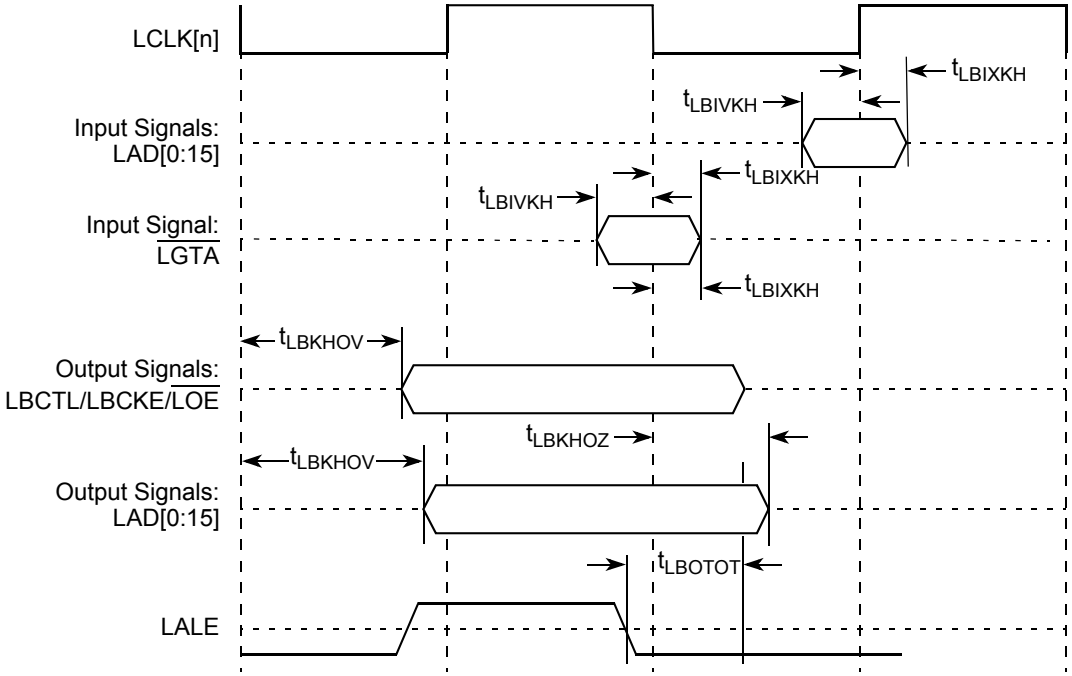

Figure 8. Local Bus Signals

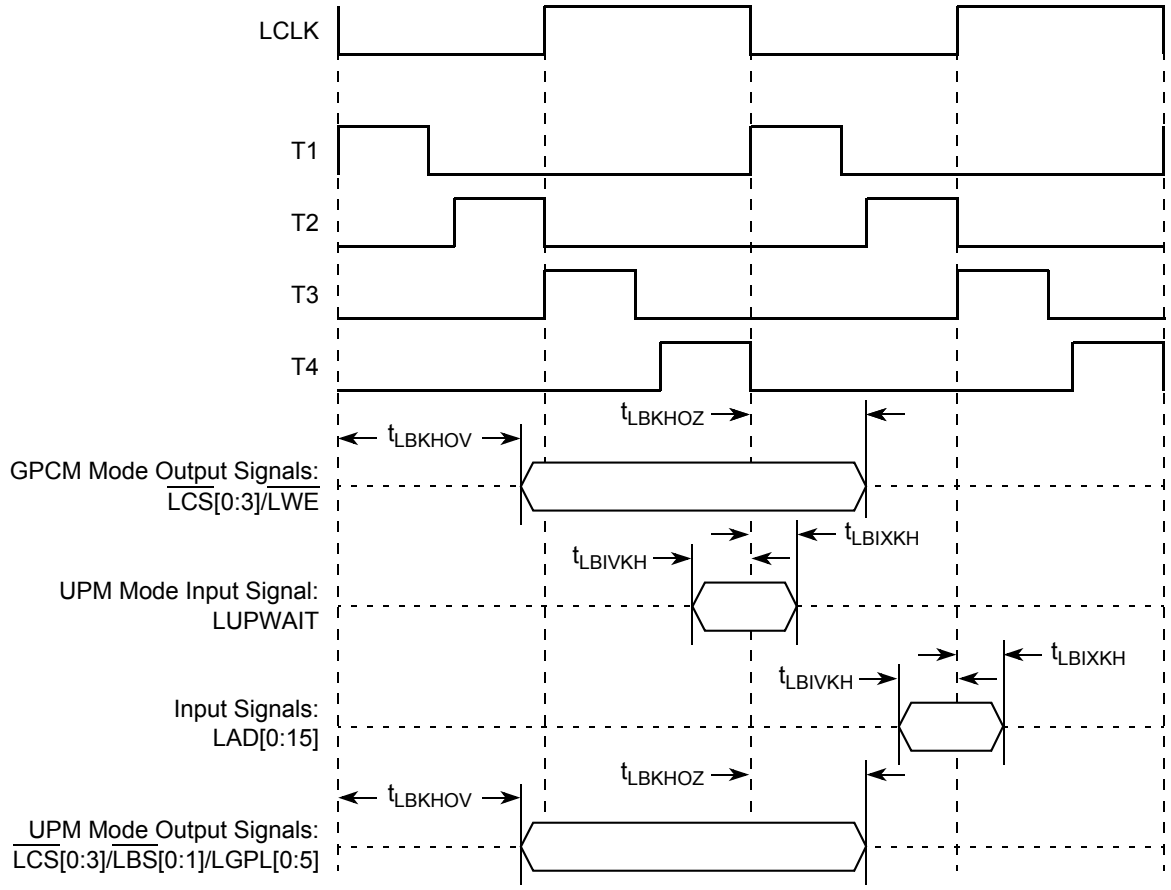

Figure 10. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4

8 Ethernet and MII Management

This section provides the AC and DC electrical characteristics for Ethernet interfaces.

8.1 Ethernet Controller (10/100 Mbps)—MII/RMII Electrical Characteristics

The electrical characteristics specified here apply to all MII (media independent interface) and RMII (reduced media independent interface), except MDIO (management data input/output) and MDC (management data clock). The MII and RMII are defined for 3.3 V. The electrical characteristics for MDIO and MDC are specified in Section 8.3, "Ethernet Management Interface Electrical Characteristics."

8.1.1 DC Electrical Characteristics

All MII and RMII drivers and receivers comply with the DC parametric attributes specified in The following table.

The following figure shows the RMII receive AC timing diagram.

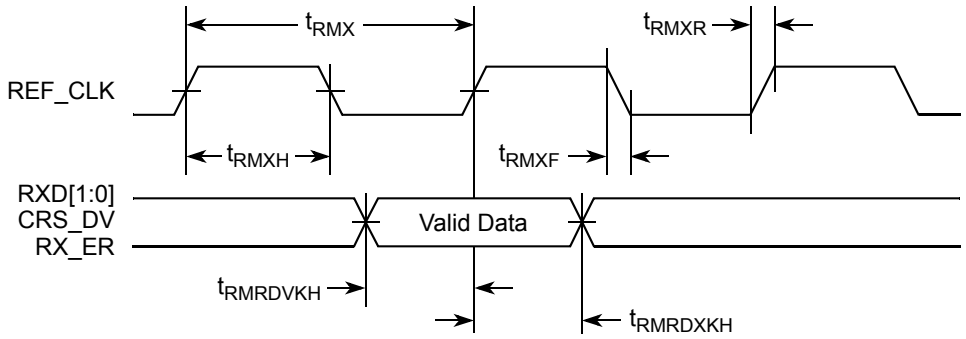

Figure 16. RMII Receive AC Timing Diagram

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for MII, and RMII are specified in Section 8.1, "Ethernet Controller (10/100 Mbps)—MII/RMII Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in the following table.

Table 24. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		3	3.6	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	OV_{DD} = Min	2.40	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±5	μA

8.3.2 MII Management AC Electrical Specifications

The following table provides the MII management AC timing specifications.

Table 25. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 300mV.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit	Note
MDC frequency	f_{MDC}	—	2.5	—	MHz	—
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—

Table 25. MII Management AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} is 3.3 V ± 300mV.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit	Note
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	—
MDIO to MDC setup time	t_{MDDVKH}	8.5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—
MDC fall time	t_{MDHF}	—	—	10	ns	—

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

The following figure shows the MII management AC timing diagram.

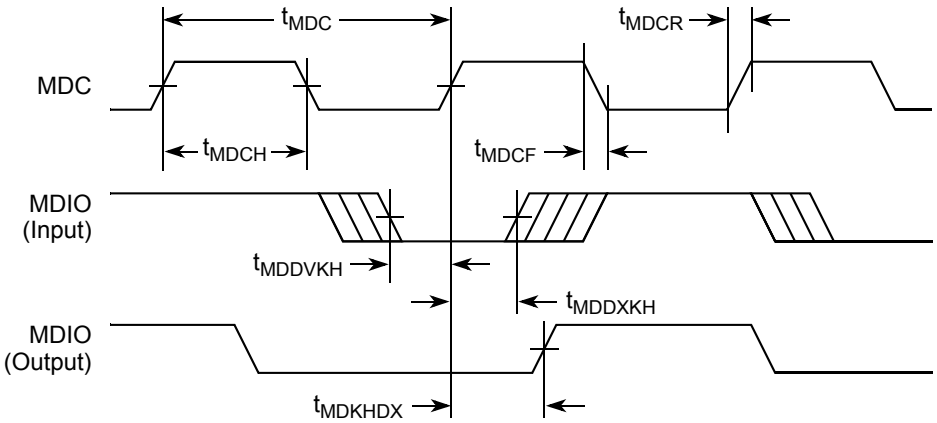

Figure 17. MII Management Interface Timing Diagram

9 TDM/SI

This section describes the DC and AC electrical specifications for the time-division-multiplexed and serial interface of the MPC8306S.

9.1 TDM/SI DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306S TDM/SI.

Table 26. TDM/SI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –2.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$	—	±5	μA

9.2 TDM/SI AC Timing Specifications

The following table provides the TDM/SI input and output AC timing specifications.

Table 27. TDM/SI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
TDM/SI outputs—External clock delay	t_{SEKHOV}	2	14	ns
TDM/SI outputs—External clock High Impedance	t_{SEKHOX}	2	10	ns
TDM/SI inputs—External clock input setup time	t_{SEIVKH}	5	—	ns
TDM/SI inputs—External clock input hold time	t_{SEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of QE_CLK_IN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{SEKHOX} symbolizes the TDM/SI outputs external timing (SE) for the time $t_{TDM/SI}$ memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

The following figure provides the AC test load for the TDM/SI.

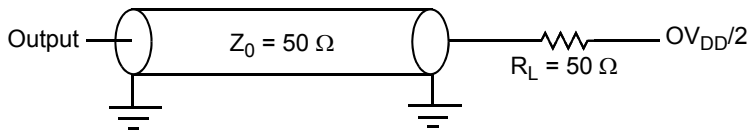

Figure 18. TDM/SI AC Test Load

Table 31. USB General Timing Parameters (continued)

Parameter	Symbol[1]	Min	Max	Unit	Note
USB clock to output valid—USBDR_STP	t_{USKHOV}	—	7.5	ns	—
Output hold from USB clock—all outputs	t_{USKHOX}	2	—	ns	—

Note:
1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{USIXKH} symbolizes USB timing (USB) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes us timing (USB) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.

The following figures provide the AC test load and signals for the USB, respectively.

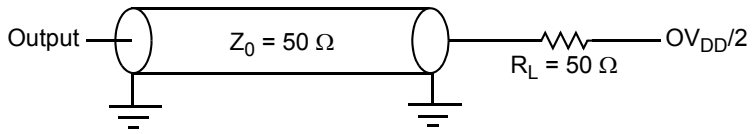

Figure 23. USB AC Test Load

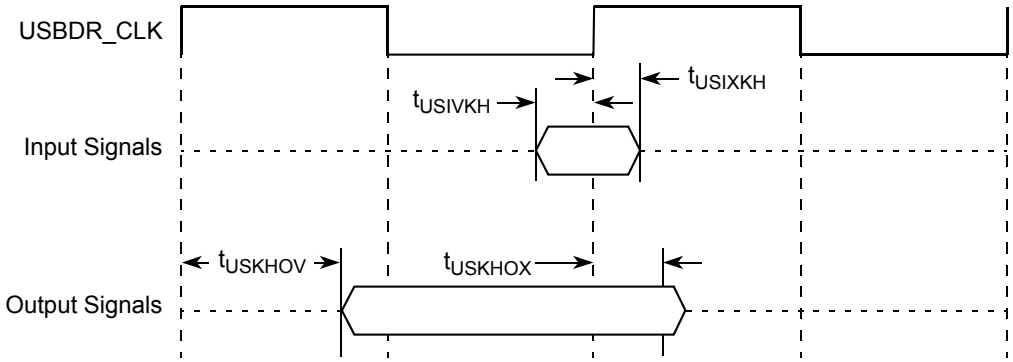

Figure 24. USB Signals

12 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8306S.

12.1 DUART DC Electrical Characteristics

The following table provides the DC electrical characteristics for the DUART interface of the MPC8306S.

Table 32. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage OV_{DD}	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V
Input current (0 V ≤ V_{IN} ≤ OV_{DD})[1]	I_{IN}	—	±5	μA

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

12.2 DUART AC Electrical Specifications

The following table provides the AC timing parameters for the DUART interface of the MPC8306S.

Table 33. DUART AC Timing Specifications

Parameter	Value	Unit	Note
Minimum baud rate	256	baud	—
Maximum baud rate	>1,000,000	baud	1
Oversample rate	16	—	2

Notes:
1. Actual attainable baud rate is limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

14 Timers

This section describes the DC and AC electrical specifications for the timers of the MPC8306S.

14.1 Timer DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306S timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_PIT_CLK.

Table 36. Timer DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$	—	±5	μA

14.2 Timer AC Timing Specifications

The following table provides the timer input and output AC timing specifications.

Table 37. Timer Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLK_IN. Timings are measured at the pin.
2. Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by any external synchronous logic. Timer inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

The following figure provides the AC test load for the timers.

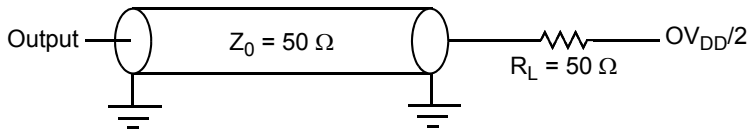

Figure 27. Timers AC Test Load

16 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8306S.

16.1 IPIC DC Electrical Characteristics

The following table provides the DC electrical characteristics for the external interrupt pins of the MPC8306S.

Table 40. IPIC DC Electrical Characteristics[1,2]

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output High Voltage	V_{OH}	I_{OL} = -8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:
1. This table applies for pins $\overline{\text{IRQ}}$, $\overline{\text{MCP\_OUT}}$, and QE ports Interrupts.
2. $\overline{\text{MCP\_OUT}}$ is open drain pins, thus V_{OH} is not relevant for those pins.

16.2 IPIC AC Timing Specifications

The following table provides the IPIC input and output AC timing specifications.

Table 41. IPIC Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
IPIC inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLK_IN. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by any external synchronous logic. IPIC inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation when working in edge triggered mode.

17 SPI

This section describes the DC and AC electrical specifications for the SPI of the MPC8306S.

17.1 SPI DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306S SPI.

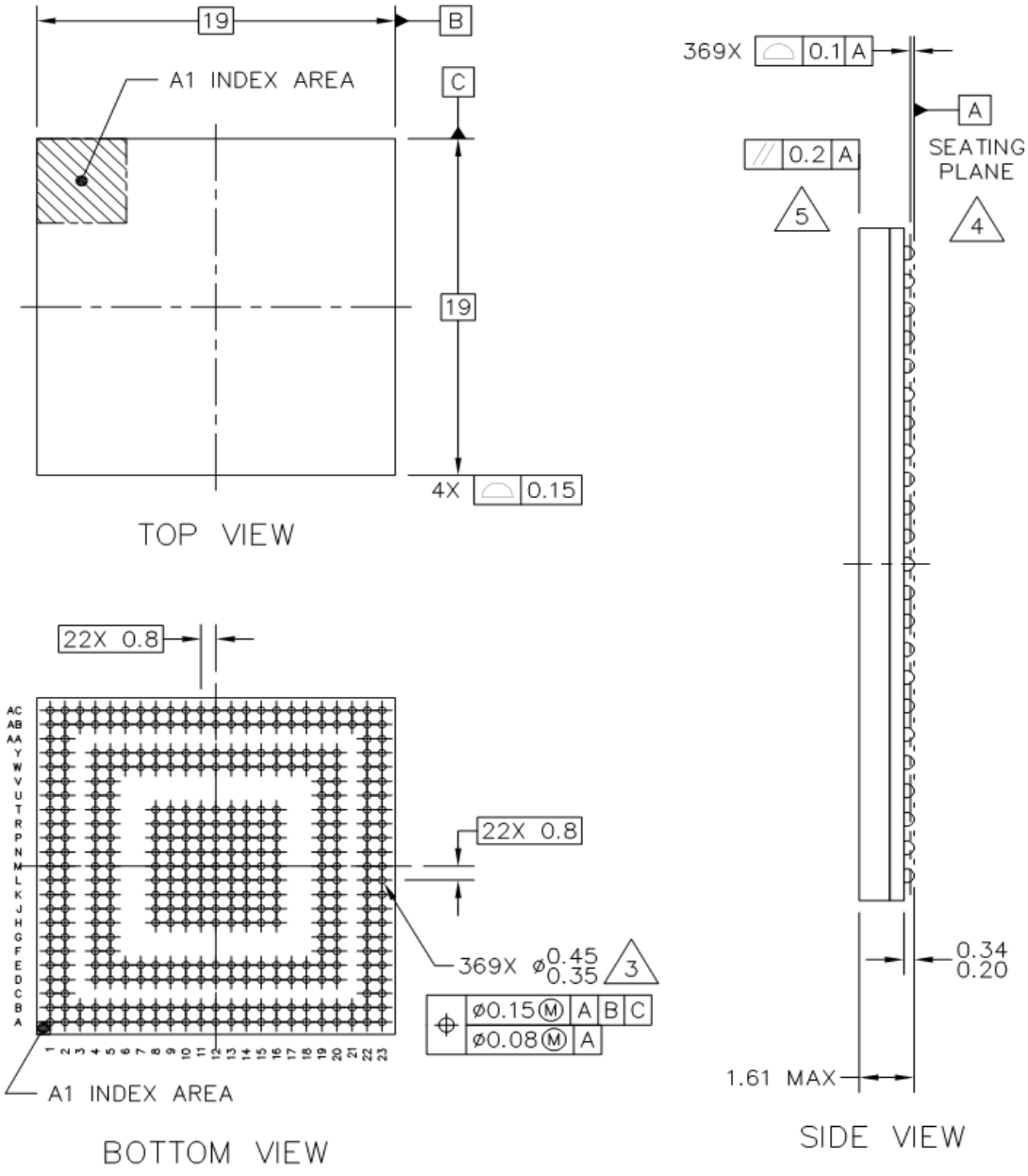

Figure 37. Mechanical Dimensions and Bottom Surface Nomenclature of the MPC8306S MAPBGA

Notes:
1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Table 46. MPC8306S Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MEMC_MA[8]	T1	O	GV_{DD}	—
MEMC_MA[9]	P4	O	GV_{DD}	—
MEMC_MA[10]	L4	O	GV_{DD}	—
MEMC_MA[11]	T2	O	GV_{DD}	—
MEMC_MA[12]	U1	O	GV_{DD}	—
MEMC_MA[13]	U2	O	GV_{DD}	—
MEMC_MWE_B	K1	O	GV_{DD}	—
MEMC_MRAS_B	K2	O	GV_{DD}	—
MEMC_MCAS_B	J1	O	GV_{DD}	—
MEMC_MCS_B[0]	J4	O	GV_{DD}	—
MEMC_MCS_B[1]	H1	O	GV_{DD}	—
MEMC_MCKE[0]	U4	O	GV_{DD}	—
MEMC_MCK[0]	V1	O	GV_{DD}	—
MEMC_MCK_B[0]	W1	O	GV_{DD}	—
MEMC_MODT[0]	H2	O	GV_{DD}	—
MEMC_MODT[1]	H4	O	GV_{DD}	—
MEMC_MVREF	L8		GV_{DD}	—
Local Bus Controller Interface				
LAD[0]	B7	IO	OV_{DD}	—
LAD[1]	D9	IO	OV_{DD}	—
LAD[2]	A6	IO	OV_{DD}	—
LAD[3]	B8	IO	OV_{DD}	—
LAD[4]	A7	IO	OV_{DD}	—
LAD[5]	A8	IO	OV_{DD}	—
LAD[6]	A9	IO	OV_{DD}	—
LAD[7]	D10	IO	OV_{DD}	—
LAD[8]	B10	IO	OV_{DD}	—
LAD[9]	A10	IO	OV_{DD}	—
LAD[10]	B11	IO	OV_{DD}	—
LAD[11]	D12	IO	OV_{DD}	—
LAD[12]	D11	IO	OV_{DD}	—
LAD[13]	A11	IO	OV_{DD}	—
LAD[14]	A12	IO	OV_{DD}	—
LAD[15]	B13	IO	OV_{DD}	—
LA[16]	A13	IO	OV_{DD}	—

Table 46. MPC8306S Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
FEC3_TXD0/TSEC_TMR_PP2/GPIO[60]	R20	IO	OV_{DD}	—
FEC3_TXD1/TSEC_TMR_PP3/GPIO[61]	T22	IO	OV_{DD}	—
FEC3_TXD2/TSEC_TMR_ALARM1/GPIO[62]	T23	IO	OV_{DD}	—
FEC3_TXD3/TSEC_TMR_ALARM2/GPIO[63]	T20	IO	OV_{DD}	—
HDLC/GPIO/TDM				
HDLC1_RXCLK/TDM1_RCK/GPIO[1]	U23	IO	OV_{DD}	—
HDLC1_RXD/TDM1_RD/GPIO[3]	U22	IO	OV_{DD}	—
HDLC1_TXCLK/GPIO[0]/TDM1_TCK/ QE_BRG[5]	AC22	IO	OV_{DD}	—
HDLC1_TXD/GPIO[2]/TDM1_TD/ CFG_RESET_SOURCE[0]	W18	IO	OV_{DD}	—
HDLC1_CD_B/GPIO[4]/TDM1_TFS	W19	IO	OV_{DD}	—
HDLC1_CTS_B/GPIO[5]/TDM1_RFS	Y20	IO	OV_{DD}	—
HDLC1_RTS_B/GPIO[6]/TDM1_STROBE_B/ CFG_RESET_SOURCE[1]	AB22	IO	OV_{DD}	—
HDLC2_TXCLK/GPIO[16]/TDM2_TCK/ QE_BRG[7]	AB23	IO	OV_{DD}	—
HDLC2_RXCLK/GPIO[17]/TDM2_RCK/ QE_BRG[8]	AA23	IO	OV_{DD}	—
HDLC2_TXD/GPIO[18]/TDM2_TD/ CFG_RESET_SOURCE[2]	W20	IO	OV_{DD}	—
HDLC2_RXD/GPIO[19]/TDM2_RD	Y23	IO	OV_{DD}	—
HDLC2_CD_B/GPIO[20]/TDM2_TFS	Y22	IO	OV_{DD}	—
HDLC2_CTS_B/GPIO[21]/TDM2_RFS	W23	IO	OV_{DD}	—
HDLC2_RTS_B/GPIO[22]/TDM2_STROBE_B/ CFG_RESET_SOURCE[3]	W22	IO	OV_{DD}	—
Power				
AV_{DD1}	L16	—	—	—
AV_{DD2}	M16	—	—	—
AV_{DD3}	N8	—	—	—
GV_{DD}	G5, H5, J5, K5, L5, M5, N5, P5, R5, T5, U5	—	—	—
OV_{DD}	E7,E8,E9,E10,E11,E12, E13,E14, E15, E16,E17,G19,H19,J19,K 19,L19,M19, N19,P19,R19,T19,U19, W7,W8,W9, W10,W11, W12,W13, W14,W15, W16, W17	—	—	—

Table 46. MPC8306S Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
V_{DD}	H8,H9,H10,H11,H12,H13,H14,H15,H16,J8,J16,K8,K16,M8,N16,P8,P16,R8,R16,T8,T9,T10,T11,T12,T13,T14,T15,T16	—	—	—
VSS	A1,B4,B6,B9,B12,B15,B18,B21,C22,D2,D5,D18,D20,F2,F22,J2,J9,J10,J11,J12,J13,J14,J15,J22,K4,K9,K10,K11,K12,K13,K14,K15,L9,L10,L11,L12,L13,L14,L15,M2,M9,M10,M11,M12,M13,M14,M15,M22,N9,N10,N11,N12,N13,N14,N15,P9,P10,P11,P12,P13,P14,P15,R2,R9,R10,R11,R12,R13,R14,R15,R22,T4,V2,V19,V22,W4,Y19,AA2,AA22,AB4,AB6,AB9,AB12,AB15,AB18,AB21,AC1,AC23	—	—	—
NC	A23	—	—	—

Notes
1. This pin is an open drain signal. A weak pull-up resistor (1 kΩ) should be placed on this pin to OV_{DD}
2. This pin is an open drain signal. A weak pull-up resistor (2-10 kΩ) should be placed on this pin to OV_{DD}
3. This pin has weak pull-up that is always enabled.

Table 49. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

coherent system bus clock (*csb_clk*). The following table shows the expected frequency values for the CSB frequency for selected *csb_clk* to *SYS_CLK_IN* ratios.

Table 50. CSB Frequency Options

SPMF	csb_clk : sys_clk_in Ratio	SYS_CLK_IN(MHz)		
		25	33.33	66.67
		csb_clk Frequency (MHz)		
0010	2:1			133
0011	3:1			
0100	4:1		133	
0101	5:1	125	167	
0110	6:1			

20.3 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). The following table shows the encodings for RCWL[COREPLL]. COREPLL values not listed, and should be considered reserved.

Table 51. e300 Core PLL Configuration

RCWL[COREPLL]			*core_clk* : *csb_clk* Ratio	VCO Divider
0-1	2-5	6		
nn	0000	n	PLL bypassed (PLL off, *csb_clk* clocks core directly)	PLL bypassed (PLL off, *csb_clk* clocks core directly)
00	0001	0	1:1	÷2
01	0001	0	1:1	÷4
10	0001	0	1:1	÷8
11	0001	0	1:1	÷8

22.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins. The voltage level at each $AV_{DD}n$ pin should always be equivalent to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide independent filter circuits as illustrated in Figure 41, one to each of the three AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

The following figure shows the PLL power supply filter circuit.

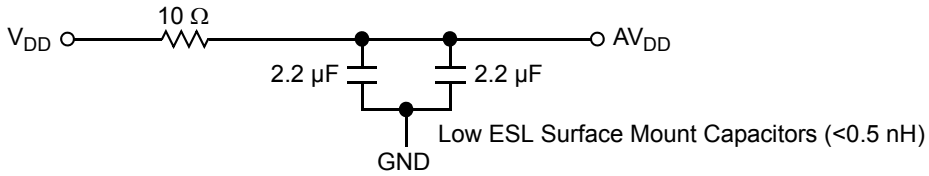

Figure 41. PLL Power Supply Filter Circuit

22.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the MPC8306S can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8306S system, and MPC8306S itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, OV_{DD}, and GV_{DD} pins of the MPC8306S. These decoupling capacitors should receive their power from separate V_{DD}, OV_{DD}, GV_{DD}, and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, OV_{DD}, and GV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias